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Appendix

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Cho Cho Thet; Sakuntam Sanorpim; Somsak Panyakeow; and Songphol Kanjanachuchai. The Effects of Relaxed InGaAs Virtual Substrates on the Formation of Self-Assembled InAs Quantum Dots. 19th International Microprocesses and Nanotechnology conference, October 24-27, Kamakura Prince Hotel, Kanagawa, Japan.

Domestic Journal

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Domestic Conference

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VITAE

Cho Cho Thet was born in Yangon, Myanmar, on January 14, 1974. She received B.Sc (Hons: Physics) and M.Sc (Physics) Degrees in Physics Department from Dagon University, Yangon, in 1999 and 2002, respectively. She got the scholarship from the "Japanese International Cooperation Agency Office (JICA) for the Southeast Asia Engineering Education Development Network of ASEAN University Network (AUN/SEED-Net)" on 15, October 2003 for the Doctoral of Engineering Degree Programme. She entered the Graduated School of Chulalongkorn University in November, 2003 as a student of the Semiconductor Device Research Laboratory (SDRL). Her interests are nanotechnology for III-V compound semiconductors.